



40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BVDSS	Rds(on) Max	I _D Max T _C = +25°C
40V	8.9mΩ @ V _{GS} = 10V	52.4A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management Functions
- DC-DC Converters

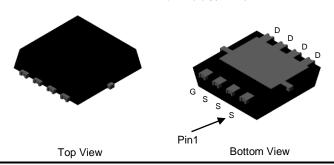
Features and Benefits

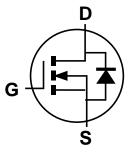
- Rated to +175°C Ideal for High Ambient Temperature Environments
- Excellent Q_{GD} × R_{DS(ON)} Product (FOM)
- Low Rds(ON) Ensures On-State Losses Minimized
- 100% Unclamped Inductive Switching, Test in Production Ensures More Reliable and Robust End Application
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMTH48M3SFVWQ</u>)

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

PowerDI3333-8 (SWP) (Type UX)





Equivalent Circuit

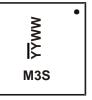
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH48M3SFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMTH48M3SFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



M3S = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 20 = 2020)

WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A =+ 25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	40	V		
Gate-Source Voltage	Vgss	±20	V		
Continuous Dusin Comment (Nata C) 1/ 401/	Tc = +25°C	1-	52.4	А	
Continuous Drain Current (Note 6), Vgs = 10V	Tc = +100°C	ID	37.1		
0 (0 (10 (10 (10 (10 (10 (10 (1	T _A = +25°C		14.6	Δ.	
Continuous Drain Current (Note 5), V _{GS} = 10V	T _A = +100°C	ID	10.3	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	209	А		
Maximum Continuous Body Diode Forward Current (Note 6)	Is	40.6	А		
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle	lsм	209	Α		
Avalanche Current, L = 0.1mH	las	24.7	Α		
Avalanche Energy, L = 0.1mH	Eas	30.5	mJ		

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5) $T_A = +25$ °C		P_{D}	2.82	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	52.6	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		PD	36.6	W
Thermal Resistance, Junction to Case (Note 6)	RеJC	4.09	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C	

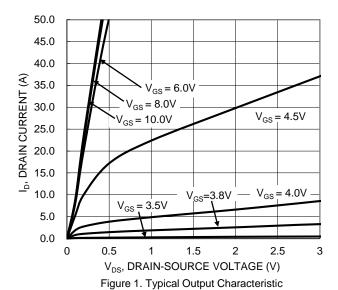
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	40	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	2.7	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	6.9	8.9	mΩ	V _{GS} = 10V, I _D = 20A	
Diode Forward Voltage	VsD	_	0.9	1.2	V	V _G S = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	897	_		V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	530	_	pF		
Reverse Transfer Capacitance	Crss	_	12.4	_			
Gate Resistance	Rg	_	2.07		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	12.1	_		V _{DS} = 20V, I _D = 20A, V _{GS} = 10V	
Gate-Source Charge	Q_{gs}	_	2.0	_	nC		
Gate-Drain Charge	Qgd	_	1.9	_			
Turn-On Delay Time	t _D (ON)	_	5.36	_		$V_{DD} = 20V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 20A$	
Turn-On Rise Time	t _R	_	4.54	_			
Turn-Off Delay Time	tD(OFF)	_	12.1	_	ns		
Turn-Off Fall Time	tF	_	5.59	_			
Body Diode Reverse Recovery Time	trr	_	39.1	_	ns	I- 200 di/dt 4000///-	
Body Diode Reverse Recovery Charge	Q _{RR}	_	53.3	_	nC	I _F = 20A, di/dt = 100A/μs	

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 5. Device involved on the state of the exposed drain pads to 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.





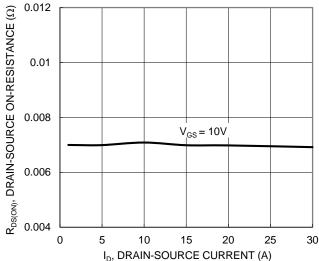


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

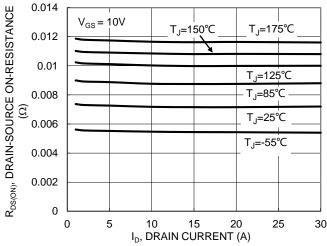
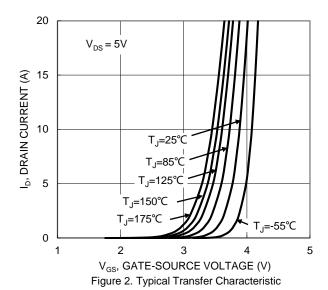
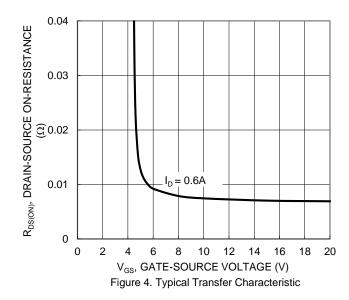


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





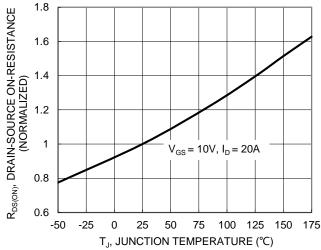


Figure 6. On-Resistance Variation with Junction Temperature



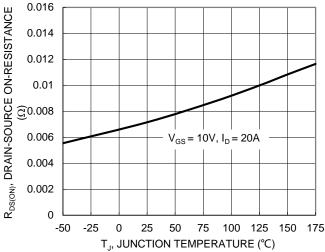
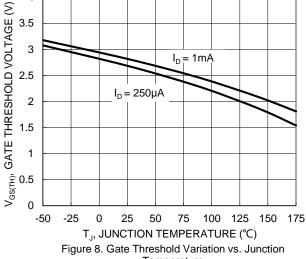


Figure 7. On-Resistance Variation with Junction Temperature



Temperature

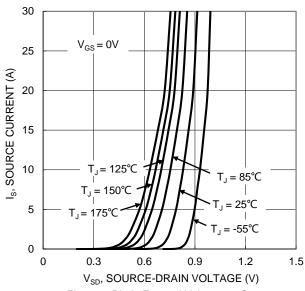
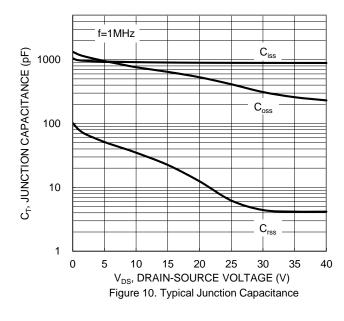
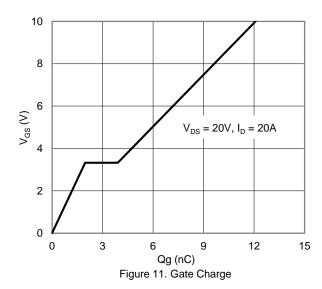
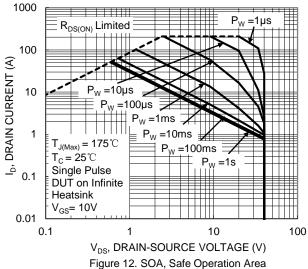


Figure 9. Diode Forward Voltage vs. Current









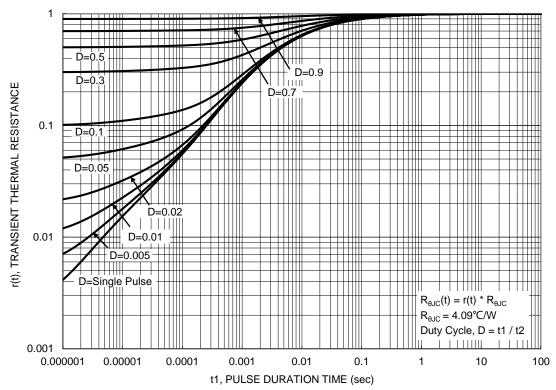


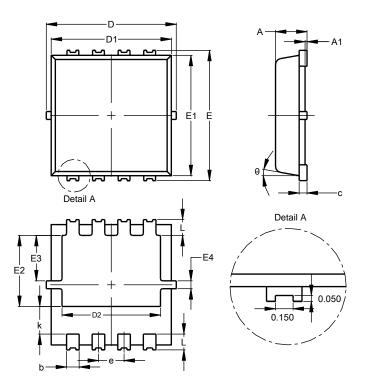
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

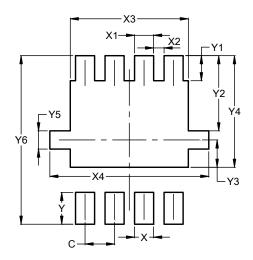


Pov	PowerDI3333-8 (SWP)					
	(Type UX)					
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	-			
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
E	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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